



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate MOSFETs

CJ2307 P-Channel 30-V(D-S) MOSFET

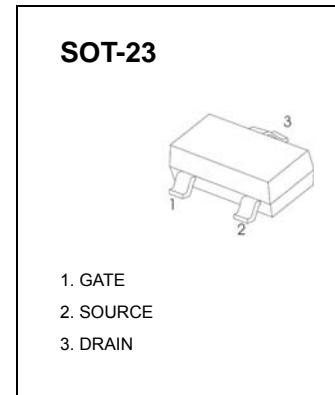
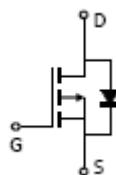
FEATURE

TrenchFET Power MOSFET

APPLICATIONS

Load Switch for Portable Devices

MARKING: S7



Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^{a,b}	I_D	-2.7	A
Continuous Source-Drain Current ^{a,b}	I_S	-0.91	
Power Dissipation ^{a,b}	P_D	1.1	W
Thermal Resistance from Junction to Ambient ($t \leq 5\text{s}$)	$R_{\theta JA}$	114	$^\circ\text{C/W}$
Operating Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	

Electrical characteristics ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = -250\mu\text{A}$	-30			V
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = -250\mu\text{A}$	-1		-3	
Gate-Source Leakage	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = -30\text{V}, V_{\text{GS}} = 0\text{V}$			-1	μA
		$V_{\text{DS}} = -30\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 55^\circ\text{C}$			-10	
Drain-Source On-State Resistance ^c	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = -4.5\text{V}, I_D = -2.5\text{A}$		0.110	0.138	Ω
		$V_{\text{GS}} = -10\text{V}, I_D = -3.5\text{A}$		0.073	0.088	
Forward Transconductance ^c	g_{fs}	$V_{\text{DS}} = -10\text{V}, I_D = -3.5\text{A}$		7		S
Dynamic^d						
Input Capacitance	C_{iss}	$V_{\text{DS}} = -15\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		340		pF
Output Capacitance	C_{oss}			67		
Reverse Transfer Capacitance	C_{rss}			51		
Total Gate Charge	Q_g	$V_{\text{DS}} = -15\text{V}, V_{\text{GS}} = -4.5\text{V}, I_D = -2.5\text{A}$		4.1	6.2	nC
Gate-Source Charge	Q_{gs}			1.3		
Gate-Drain Charge	Q_{gd}			1.8		
Gate Resistance	R_g	$f = 1\text{MHz}$		10		Ω
Turn-On Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = -15\text{V}, R_L = 15\Omega, I_D = -1\text{A}, V_{\text{GEN}} = -4.5\text{V}, R_g = 1\Omega$		40	60	ns
Rise Time	t_r			40	60	
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$			20	40	
Fall Time	t_f			17	30	
Drain-source Body diode characteristics						
Body Diode Voltage	V_{SD}	$I_S = -0.75\text{A}, V_{\text{GS}} = 0$		-0.8	-1.2	V

Notes:

- a. t=5s.
- b. Surface mounted on 1" × 1" FR4 board.
- c. Pulse Test : Pulse Width < 300μs, Duty Cycle ≤2%.
- d. Guaranteed by design, not subject to production testing.

Typical Characteristics

CJ2307

